



Session Title:	[WA1] Advanced Atomic Scale Thin Films VI
Session Date:	November 22 (Wed.), 2023
Session Time:	08:30-10:10
Session Room:	Room A (Capri Room, 2F)
Session Chair:	Prof. Se Hun Kwon (Pusan Nat'l Univ., Korea)

[WA1-1] 08:30-08:50

Characteristics for IGZO Films Deposited with New In & Ga Precursors

J. H. Kim, S. Y. Jeon, S. D. Lee, G. S. Lee, Y. H. Kwone, Y. J. Im, and S. I. Lee (DNF Co. Ltd., Korea)

[WA1-2] 08:50-09:10

Effects of Plasma Enhanced Chemical Vapor Deposition Parameters on Silicon Oxide Thin Film Characteristics and Its Warpage

Dow Wook Lee (Hanyang Univ., Korea), Hyun Na Bae, Seon Kyu Kim (Samsung Electronics Co., Ltd., Korea), and Hyeongtag Jeon (Hanyang Univ., Korea)

[WA1-3] 09:10-09:30

Enhanced Metal/Dielectric Selectivity in Ru Atomic Layer Deposition with Alkyl-Chain Length Dependent Phosphonic Acid Self-Assembled Monolayers

Seo-Hyun Lee, Jeong-Min Lee, and Woo-Hee Kim (Hanyang Univ., Korea)

[WA1-4] 09:30-09:50

Modulating ALD Molybdenum Oxide Film Properties for DRAM Application through Controlled Oxidants and H₂ Annealing with Mo(NMe₂)₄ Precursor

Hae Lin Yang, Ara Yoon, Sanghoon Lee, and Jin-Seong Park (Hanyang Univ., Korea)

[WA1-5] [Invited] 09:50-10:10

Ozone Concentration Dependence of Tetragonal Phase of ZrO₂

Seokhwi Song, Eungju Kim, Kyunghoo Kim, and Hyeongtag Jeon (Hanyang Univ., Korea)